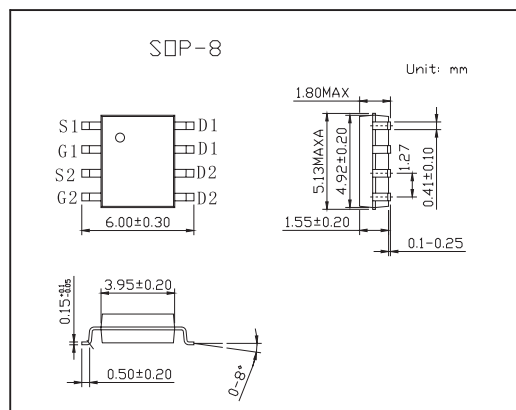
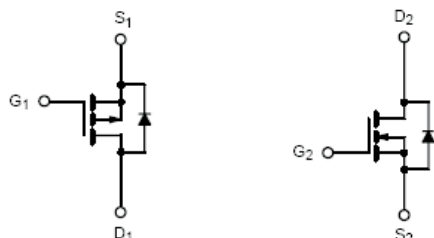


N- and P-Channel MOSFET

KI4503DY

■ Features

- TrenchFET Power MOSFET



■ Absolute Maximum Ratings TA = 25°C

Parameter	Symbol	N-Channel		P-Channel		Unit		
		10 sec	Steady State	10 sec	Steady State			
Drain-Source Voltage	V _{DS}	30		-8		V		
Gate-Source Voltage	V _{GS}	±20		±8		V		
Continuous Drain Current (T _J = 150°C)* TA = 25°C	I _D	8.8	6.3	-4.5	-3.8	A		
		TA = 70°C		7	5.2	-3.6	-3	A
Pulsed Drain Current	I _{DM}	30		-20		A		
Continuous Source Current (Diode Conduction)*	I _S	2	1.1	-1.2	0.9	A		
Maximum Power Dissipation*	P _D	TA = 25°C		2.27	1.25	1.38	1	W
		TA = 70°C		1.45	0.8	0.88	0.64	W
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150				°C		

*Surface Mounted on FR4 Board; t ≤ 10 sec.

■ Thermal Resistance Ratings TA = 25°C

Parameter	Symbol	N-Channel		P-Channel		Unit		
		Typ	Max	Typ	Max			
Maximum Junction-to-Ambient*	R _{thJA}	t ≤ 10 sec		45	55	75	90	°C/W
		Steady State		85	100	100	125	
Maximum Junction-to-Foot	R _{thJc}	25	30	53	65			

*Surface Mounted on FR4 Board.

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■ Electrical Characteristics $T_J = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	N-Ch	0.8			V
		$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	P-Ch	-0.45			
Gate Body Leakage	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$	N-Ch			± 100	nA
		$V_{DS} = 0\text{V}, V_{GS} = \pm 8\text{V}$	P-Ch			± 100	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}$	N-Ch			1	
		$V_{DS} = -6.4\text{V}, V_{GS} = 0\text{V}$	P-Ch			-1	
		$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}, T_J = 55^\circ\text{C}$	N-Ch			5	μA
		$V_{DS} = -6.4\text{V}, V_{GS} = 0\text{V}, T_J = 55^\circ\text{C}$	P-Ch			-5	
On State Drain Currenta	$I_{D(on)}$	$V_{DS} = 5\text{V}, V_{GS} = 10\text{V}$	N-Ch	30			A
		$V_{DS} = -5\text{V}, V_{GS} = -4.5\text{V}$	P-Ch	-20			
Drain Source On State Resistance*	$r_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 8.8\text{A}$	N-Ch		0.015	0.018	Ω
		$V_{GS} = -4.5\text{V}, I_D = -4.5\text{A}$	P-Ch		0.034	0.042	
		$V_{GS} = 4.5\text{V}, I_D = 7.2\text{A}$	N-Ch		0.022	0.027	
		$V_{GS} = -2.5\text{V}, I_D = -3.7\text{A}$	P-Ch		0.048	0.060	
Forward Transconductance*	g_{fs}	$V_{DS} = 15\text{V}, I_D = 8.8\text{A}$	N-Ch		20		S
		$V_{DS} = -15\text{V}, I_D = -4.5\text{A}$	P-Ch		13		
Diode Forward Voltage*	V_{SD}	$I_S = 2.0\text{A}, V_{GS} = 0\text{V}$	N-Ch		0.71	1.1	V
		$I_S = -1.2\text{A}, V_{GS} = 0\text{V}$	P-Ch		-0.70	-1.1	
Total Gate Charge	Q_g	N-Channel $V_{DS} = 15\text{V}, V_{GS} = 5\text{V}, I_D = 8.8\text{A}$	N-Ch		14.5	20	nC
Gate Source Charge	Q_{gs}	P-Channel $V_{DS} = -4\text{V}, V_{GS} = -5\text{V}, I_D = -4.5\text{A}$	N-Ch		3.3		
Gate Drain Charge	Q_{gd}		P-Ch		3.0		
			N-Ch		6.6		
Turn On Time	$t_{d(on)}$	N Channel $V_{DD} = 15\text{V}, R_L = 15\Omega$	N-Ch		13	20	ns
Rise Time	t_r	$I_D = 1\text{A}, V_{GEN} = 10\text{V}, R_g = 6\Omega$	P-Ch		20	40	
			N-Ch		9	18	
Turn Off Delay Time	$t_{d(off)}$	P-Channel $V_{DD} = -4\text{V}, R_L = 4\Omega$	N-Ch		35	50	
			P-Ch		110	220	
Fall Time	t_f	$I_D = -1\text{A}, V_{GEN} = -4.5\text{V}, R_g = 6\Omega$	N-Ch		17	30	
			P-Ch		60	120	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 1.7\text{A}, di/dt = 100\text{A}/\mu\text{s}$	N-Ch		35	70	
			P-Ch		60	100	

* Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.